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2 **A novel CMP application on the fabrication of dual-damascene struc advanced copper/low-k interconnections**
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[Abstract]   [PDF Full-Text (352 KB)] **CNF**

3 **Stopper-less hybrid low-k/Cu DD structure fabrication combined w CMP**
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Interconnect Technology Conference, 2002. Proceedings of the IEEE 2002 International , 2002
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L Number	Hits	Search Text	DB	Time stamp
-	5049	(hard same mask$3) and (trench via hole c ntact p n$3 groov$ reces$4 plug)	USPAT	2002/12/09 16:30
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-	1147	((trench via hole contact open$3 groov$ reces$4 plug) and (hard same mask$3) and (resist photoresist)) and ((trench via hole contact open$3 groov$ reces$4 plug) same (hard adj2 mask$3))	USPAT	2002/10/21 13:36
-	105	((trench via hole contact open$3 groov$ reces$4 plug) same (hard same mask$3) and (resist photoresist)) and (second same (hard same mask$3))	EPO; JPO; DERWENT; IBM_TDB	2002/10/21 13:50
-	90	((trench via hole contact open$3 groov$ reces$4 plug) same (hard same mask$3) and (resist photoresist)) and (second same (hard adj2 mask$3))	EPO; JPO; DERWENT; IBM_TDB	2002/10/21 13:50
-	10	(((trench via hole contact open$3 groov$ reces$4 plug) same (hard same mask$3) and (resist photoresist)) and (second same (hard adj2 mask$3))) and (second adj2 (hard adj2 mask$3))	EPO; JPO; DERWENT; IBM_TDB	2002/10/21 13:52
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-	1731	(etch$3 same (hard adj2 mask$3)) and (trench via hole open$3)	USPAT	2002/11/07 17:15
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-	135	((((tch$3 sam (hard adj2 mask$3)) and (trench via h le pen$3)) and (sec nd sam hard)) and partial$9) and (partial$9 sam hard)	USPAT	2002/11/07 17:19
-	835	438/624.ccls.	USPAT	2002/12/09 16:37
-	536	438/620,629.ccls.	USPAT	2002/12/09 16:29
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-	1001	257/774.ccls.	USPAT	2002/12/09 16:44